

# **Depletion-Mode Power MOSFET**

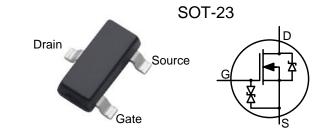
## **General Features**

- > ESD improved Capability
- > Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- > RoHS Compliant
- > Halogen-free available

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- > Synchronous Rectification
- Normally-on Switches
- ➤ Linear Amplifier
- ➤ High Voltage Regulator
- Constant Current Source
- Protection Circuits
- > Telecom

BV <sub>DSX</sub>	RDS(ON) (Max.)	I <sub>DSS</sub> ,min
150V	25 Ω	100mA



**Ordering Information** 

Part Number	Package	Marking	Remark
DMZ1511E	SOT-23	1511	Halogen Free

# **Absolute Maximum Ratings**

 $T_A=25$ °C unless otherwise specified

Symbol	Parameter	DMZ1511E	Unit
$V_{\mathrm{DSX}}$	Drain-to-Source Voltage <sup>[1]</sup>	150	V
$V_{DGX}$	Drain-to-Gate Voltage <sup>[1]</sup>	150	V
$I_D$	Continuous Drain Current	0.1	Λ
$I_{DM}$	Pulsed Drain Current <sup>[2]</sup>	0.4	A
$P_D$	Power Dissipation	0.50	W
$V_{GS}$	Gate-to-Source Voltage	±20	V
$T_{\rm L}$	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	$^{\circ}$
$T_{\text{J}}$ and $T_{\text{STG}}$	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

## **Thermal Characteristics**

Symbol	Parameter	DMZ1511E	Unit
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	250	K/W



# **Electrical Characteristics**

#### **OFF** Characteristics

T<sub>A</sub> =25°C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
$BV_{DSX}$	Drain-to-Source Breakdown Voltage	150	1		V	$V_{GS}$ =-5V, $I_D$ =250 $\mu$ A
				10	μΑ	$V_{DS}=150V$ , $V_{GS}=-5V$
$I_{D(OFF)}$	Drain-to-Source Leakage Current			1.0	mA	$V_{DS} = 150V$ , $V_{GS} = -5V$ $T_{J} = 125$ °C
τ.	Cata to Source Leakage Current	to to Source Leeke as Current	^	$V_{GS} = +20V, V_{DS} = 0V$		
$I_{GSS}$	Gate-to-Source Leakage Current			-20	μA	$V_{GS}$ =-20V, $V_{DS}$ =0V

## **ON Characteristics**

 $T_A = 25^{\circ}C$  unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
$I_{DSS}$	Saturated Drain-to-Source Current	100			mA	$V_{GS}=0V, V_{DS}=25V$
R <sub>DS(ON)</sub>	Static Drain-to-Source On-Resistance			25	Ω	$V_{GS}=0V$ , $I_D=50mA^{[3]}$
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-3.3		-1.5	V	$V_{DS}=3V$ , $I_D=8\mu A$
gfs	Forward Transconductance		0.24		S	V <sub>DS</sub> =10V, I <sub>D</sub> =50mA

# **Dynamic Characteristics**

Essentially independent of operating temperature

<u> </u>					J I	dent of operating temperature	
Symbol	Parameter	Min.	Тур.	Max.	Unit	<b>Test Conditions</b>	
C <sub>ISS</sub>	Input Capacitance		12.8		pF	V <sub>GS</sub> =-10V	
Coss	Oput Capacitance		5.4			$V_{DS}=25V$ f=1.0MHz	
$C_{RSS}$	Reverse Transfer Capacitance		3.3				
Q <sub>G</sub>	Total Gate Charge		3				
Q <sub>GS</sub>	Gate-to-Source Charge		0.23		nC	$V_{GS}$ =-10V~0V $V_{DS}$ =75V, $I_D$ =100mA	
$Q_{\mathrm{GD}}$	Gate-to-Drain (Miller) Charge		1.1				

# **Resistive Switching Characteristics**

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time		7	1		
t <sub>rise</sub>	Rise Time		16		na	$V_{GS}=-10V\sim0V$
t <sub>d(OFF)</sub>	Turn-off Delay Time		25		ns	$V_{DD}$ =75V, $I_D$ =100mA $R_G$ =20 $\Omega$
t <sub>fall</sub>	Fall Time		120			





# **Source-Drain Diode Characteristics**

T<sub>A</sub>=25°C unless otherwise specified

Symbol	Parameter	Min	Тур.	Max.	Units	Test Conditions
$V_{\mathrm{SD}}$	Diode Forward Voltage			1.2	V	I <sub>SD</sub> =100mA, V <sub>GS</sub> =-5V

## NOTE:

- [1]  $T_J = +25^{\circ}C$  to  $+150^{\circ}C$
- [2] Repetitive rating, pulse width limited by maximum junction temperature.
- [3] Pulse width≤380µs; duty cycle≤2%.



# **Typical Characteristics**

Figure 1. Maximum Power Dissipation vs.

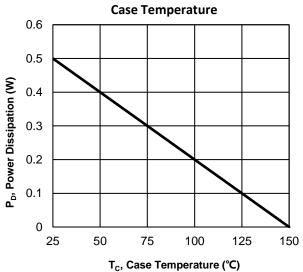
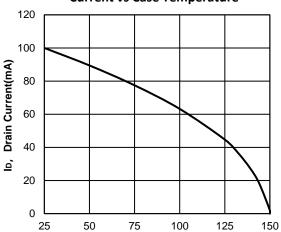
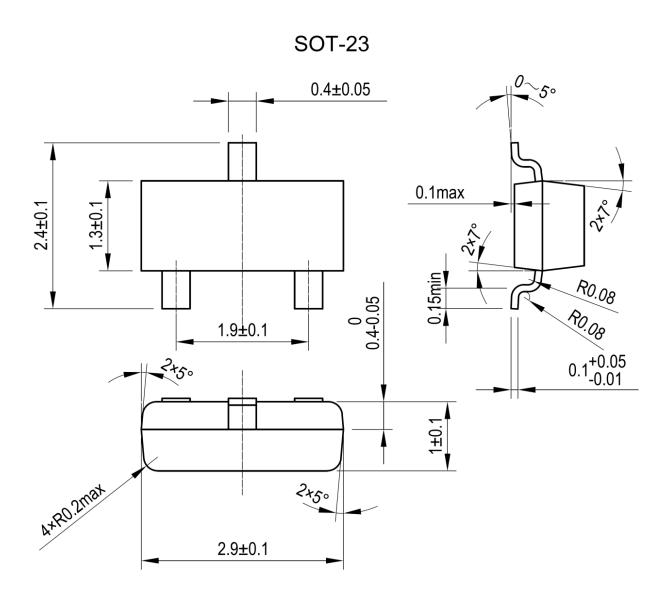


Figure 2. Maximum Continuous Drain Current vs Case Temperature



Tc, Case Temperature(°C)









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